2SC2230 TRANSISTOR (NPN)

FEATURES

Power dissipation

P_{CM}: 0.8W (Tamb=25ºC)

Collector Current

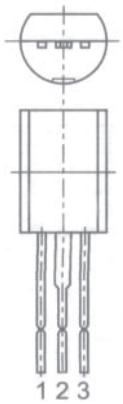
I_{CM}: 0.1A

Collector-base voltage

$V_{(BR)\ CBO}$: 200V

Operating and storage junction temperature range

T_J, T_{stg}: -55ºC to + 150ºC



TO-92 MOD

1. EMITTER
2. COLLECTOR
3. BASE

ELECTRICAL CHARACTERISTICS

(Tamb=25ºC unless otherwise specified)

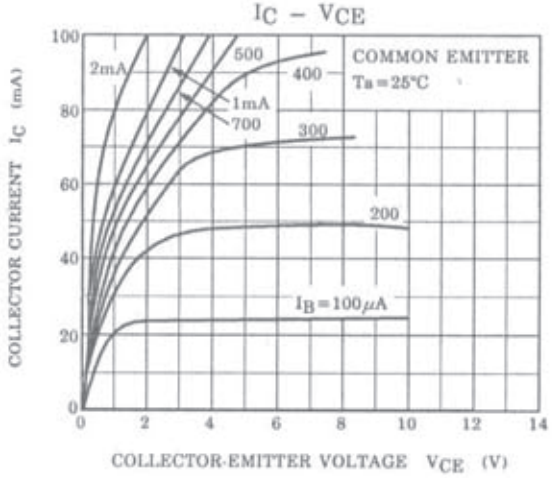
Parameter	Symbol	Test Conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)\ CBO}$	I_C= 100 µA, I_E=0	200		V
Collector-emitter breakdown voltage	$V_{(BR)\ CEO}$	I_C= 10mA, I_B=0	160		V
Emitter-base breakdown voltage	$V_{(BR)\ EBO}$	I_E= 10 µA, I_C=0	5		V
Collector cut-off current	I_{CBO}	V_{CB}= 200V, I_E=0		0.1	µA
Collector cut-off current	I_{CER}	V_{CB}= 160V, R_{EB}=10MΩ		10	µA
Emitter cut-off current	I_{EBO}	V_{EB}= 5V, I_C=0		0.1	µA
DC current gain	h_{FE}	V_{CE}= 10V, I_C= 10mA	120	400	
Collector-emitter saturation voltage	V_{CEsat}	I_C= 50A, I_B= 5mA		0.5	V
Base-emitter voltage	V_{BEsat}	I_C= 1mA, V_{CE}= 10V		0.7	V
Transition frequency	f_T	V_{CE}= 10V, I_C= 10mA	50		MHz

CLASSIFICATION OF h_{FE}

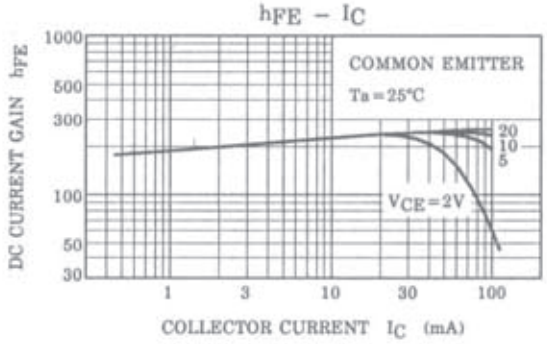
Rank	Y	GR
Range	120-240	200-400

TYPICAL CHARACTERISTICS

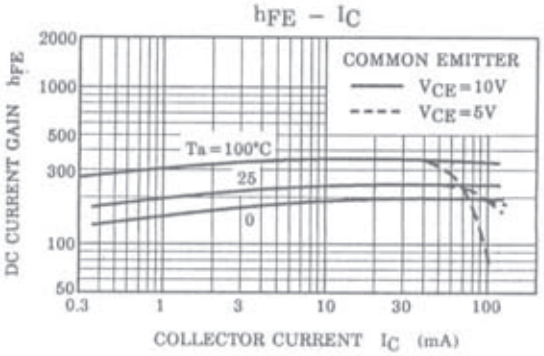
$I_C - V_{CE}$



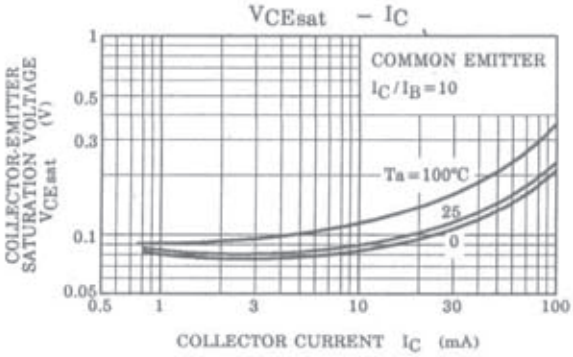
$h_{FE} - I_C$



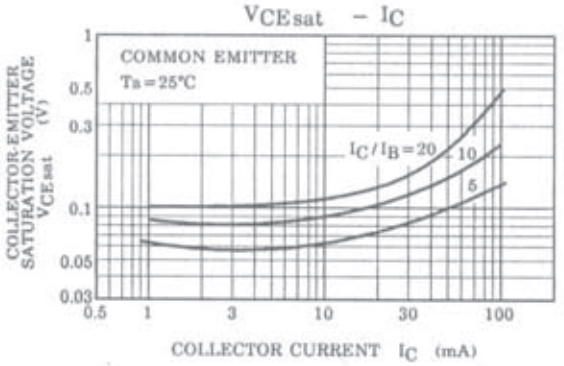
$h_{FE} - I_C$



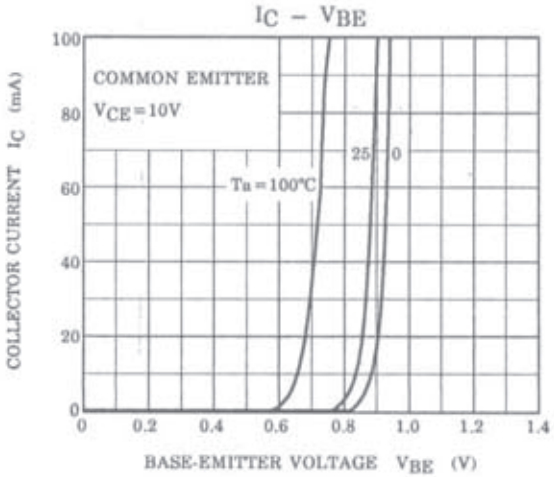
$V_{CEsat} - I_C$



$V_{CEsat} - I_C$



$I_C - V_{BE}$



VOLTTS Componentes Eletrônicos

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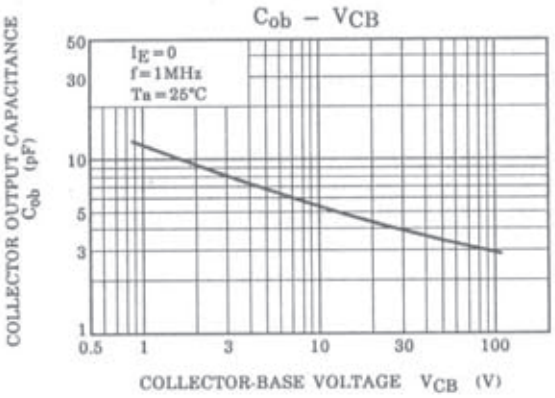
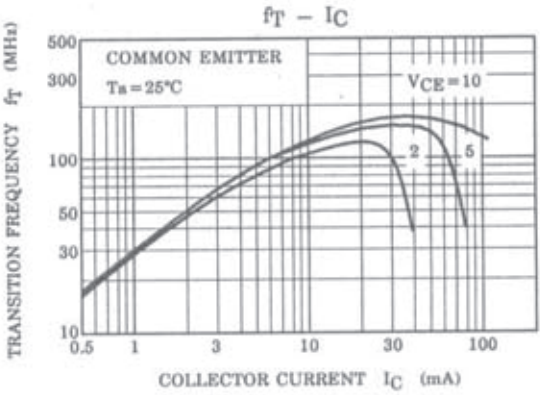
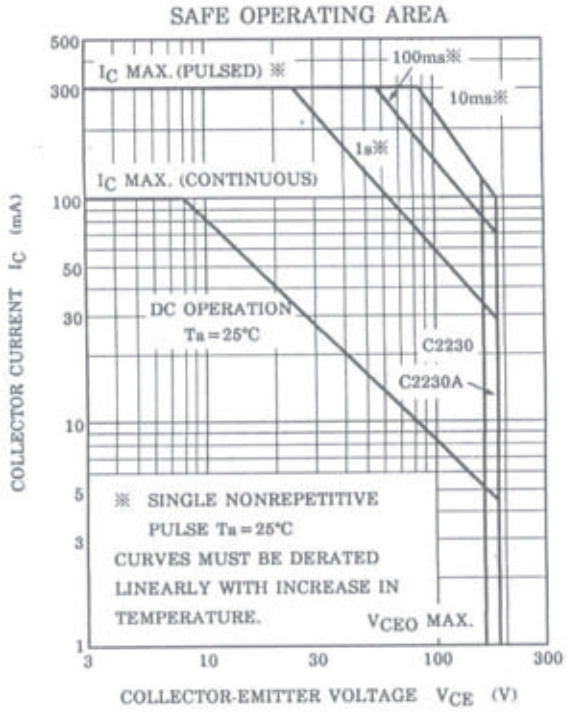
TYPICAL CHARACTERISTICS







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